IN THE CLAIMS:

Please amend claims 1, 4, 5, 9 and 10 as follows:

1. (Amended) A semiconductor device having a plurality of resistor elements formed on an insulating film in predetermined regions on a surface of a semiconductor substrate, said semiconductor device comprising

active regions proximate to each of said resistor elements.

4. (Amended) A semiconductor device having a plurality of resistor elements formed on an insulating film in predetermined regions on a surface of a semiconductor substrate, said semiconductor device comprising:

active regions proximate to each of said resistor elements, wherein

said plurality of resistor elements are arranged on said insulating film,

said insulating film under said resistor elements is set to a predetermined width by said active regions, wherein said predetermined width is defined by an amount of shift in resistance value of said resistor elements, said amount of shift being defined by said predetermined width.

5. (Amended) A semiconductor device having a plurality of resistor elements formed on an insulating film in predetermined regions on a surface of a semiconductor substrate, said semiconductor device comprising:

active regions proximate to each of said resistor elements, wherein

the regions including said active regions are furnished with dummy gate electrodes constituting the same layer as that of said resistor elements.

9. (Amended) A semiconductor device according to claim 5, wherein a plurality of said resistor elements are furnished between any adjacent two of said active regions.

10. (Amended) A semiconductor device according to claim 9, wherein a distance between any adjacent two of said plurality of resistor elements is set to a shortest distance between patterns formed by conductive film constituting the same layer as that of said resistor elements on said semiconductor substrate.

Please add the following new claim:

--21. (New) A semiconductor device according to claim 9, wherein a distance between any adjacent two of said plurality of resistor elements is set to approximately equal to a distance between any adjacent pair of said resistor elements and said dummy gate electrodes.--

IN THE DRAWINGS:

Please amend the drawings as indicated in the attached Request for Approval of Drawing Amendment.

REMARKS

At the time of the Office Action dated April 5, 2002, claims 1-20 were pending in this application. Of those claims, claims 1-3, 9-11, and 13 have been rejected and claims 14-20 have been withdrawn from consideration pursuant to the provisions of 37 C.F.R. § 1.142(b). Applicants also acknowledge, with appreciation, the Examiner's indication that claims 4-8 and